

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	"5323035".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 17:56
S2	2	"20040021476"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 18:53
S3	14836	substrate same bulk same silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 19:12
S4	1365	S3 and probe	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 18:54
S5	572	S4 and bulk adj silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 18:55
S6	6	S5 and apex\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 18:55
S7	228	S4 and bulk adj silicon same advantage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 19:00
S8	122	S4 and bulk adj silicon same advantage	USPAT	ADJ	ON	2006/12/06 18:58

## EAST Search History

S9	0	S7 and "324"/\$.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 18:58
S10	0	S7 and probe.ab.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 18:59
S11	5	S7 and probe.clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 18:59
S12	223	S4 and bulk adj silicon same advantage and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 19:00
S13	88	S12 and @py<"2003"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 19:04
S14	8	324/754.ccls. and bulk adj silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 19:04
S15	582	substrate same bulk same silicon with advantage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 19:12
S16	229	substrate same bulk adj silicon with advantage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 19:13

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S17	154	substrate same bulk adj silicon with advantage and @py<"2004"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 20:03
S18	13	"324"/\$.ccls. and contact same bulk adj silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 20:11
S19	446	"438"/\$.ccls. and contact same bulk adj silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 20:12
S20	25	S19 and probe	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 20:23
S21	2	"5323035".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 20:30
S22	4281	bulk adj semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/07 11:07
S23	2786	bulk adj semiconductive adj material	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/06 20:30
S24	46	S23 and probe	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/07 15:14

## EAST Search History

S25	109	monocrystalline adj silicon and 324/754-762.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/07 15:15
S26	2	"5420314".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/07 15:15
S27	2	"5520314".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/07 15:15
S28	2	"4520314".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/07 15:16
S29	2	"5323035".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/07 15:21
S30	2	"20040021476"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/08 11:38
S31	446	"438"/\$.ccls. and contact same bulk adj silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/08 11:38
S32	5	S31 and apex	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/08 11:38

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S33	20	isla.xa.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/11 10:44
S34	2	"5323035".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/07 11:46
S35	3008	bulk adj semiconductive adj material	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/07 11:46
S36	1257	bulk adj semiconductive adj material same monocrystalline adj silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/07 11:47
S37	46	bulk adj semiconductive adj material with monocrystalline adj silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/07 11:48
S40	2	"20040021476"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/07 12:04
S41	2	"4520314".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/07/07 12:04